RF AMPLIFIER
MODEL *TM3019*

Available as: TM3019, 4 Pin TO-8 (T4)
TN3019, 4 Pin Surface Mount (SM3)
BX3019, Connectorized Housing (H1)

Features

- GaAs FET Amplifier
- High Output Power: +22 dBm Typical
- Operating Temp. - 30 ºC to + 71 ºC
- Environmental Screening Available

Specifications

CHARACTERISTIC	TYPICAL Ta= 25 ºC	MIN/MAX Ta = -30 ºC to +71 ºC
Frequency	500 - 1300 MHz	500 - 1300 MHz
Gain (dB)	13.5	12.5 Min.
Power @ 1 dB Comp. (dBm)	+22	+21 Min.
Reverse Isolation (dB)	-21.5	-20 Max.
VSWR In Out	<1.75:1 <1.5:1	2.2:1 Max. 2.0:1 Max.
Noise Figure (dB)	2.2	3.0 Max.
Power Vdc mA	+15 105	+15 110 Max.

Note: Care should always be taken to effectively ground the case of each unit.

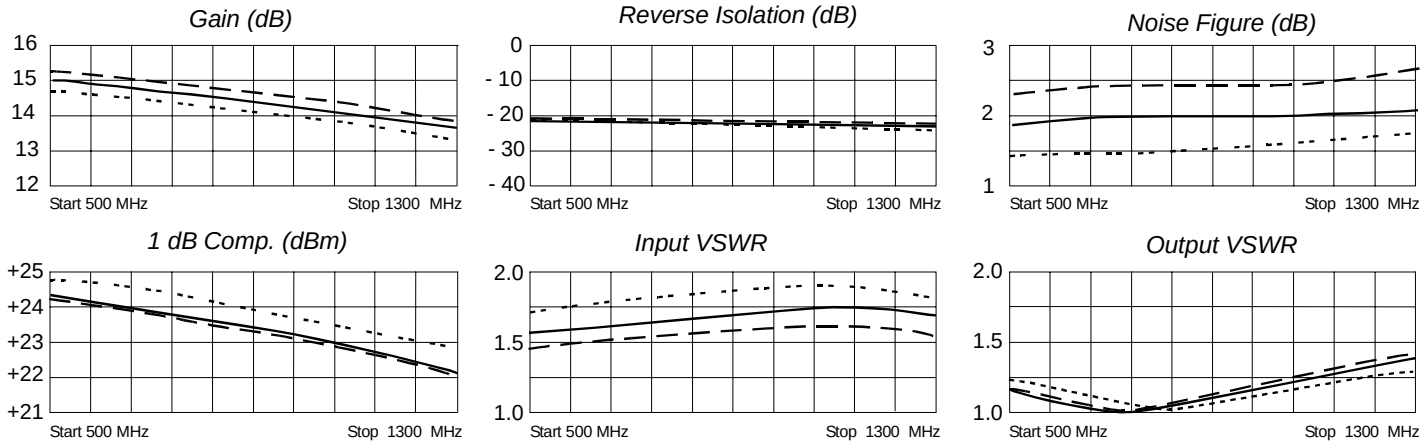
Typical Intermodulation Performance at 25 º C

Second Order Harmonic Intercept Point ..... +55 dBm (Typ.)
Second Order Two Tone Intercept Point ..... +50 dBm (Typ.)
Third Order Two Tone Intercept Point ..... +36 dBm (Typ.)

Maximum Ratings

Ambient Operating Temperature ..... -55ºC to + 100 ºC
Storage Temperature ..... -62ºC to + 125 ºC
Case Temperature ..... + 125 ºC
DC Voltage ..... + 18 Volts
Continuous RF Input Power ..... + 20 dBm
Short Term RF Input Power .... 200 Milliwatts (1 Minute Max.)
Maximum Peak Power ..... 0.5 Watt (3 µsec Max.)

Typical Performance Data



Legend ——— *+ 25 ºC* – – – *+ 71 ºC* - - - - - - *-30 ºC*

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